

Q5 代替検討SMD型に変更  
現行品使用型番:KSD1588 onsemi  
詳細  
•NPN パソジンタ

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	7	A
$I_{CP}$	*Collector Current (Pulse)	15	A
$I_B$	Base Current	3.5	A
$P_C$	Collector Dissipation ( $T_a=25^\circ\text{C}$ )	2	W
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	30	W
$T_J$	Junction Temperature	150	°C
$T_{STG}$	Storage Temperature	-55 ~ 150	°C

\* PW≤300μs, Duty Cycle≤10%

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 80\text{V}, I_E = 0$	10		μA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$	10		μA
$h_{FE1}$	* DC Current Gain	$V_{CE} = 1\text{V}, I_C = 3\text{A}$	40	200	
$h_{FE2}$		$V_{CE} = 1\text{V}, I_C = 5\text{A}$	20		
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 5\text{A}, I_B = 0.5\text{A}$	0.5		V
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage	$I_C = 5\text{A}, I_B = 0.5\text{A}$	1.5		V

代替型番DPak(TO-252-3)

NJVMJD44H11RLG onsemi  
MJD44H11AJ Nexperia  
MJD41C-QJ Nexperia

Q6 代替検討SMD型に変更  
現行品使用型番:KSB1097 Fairchild Semiconductor  
詳細  
•PNP パソジンタ

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current (DC)	-7	A
$I_{CP}$	*Collector Current (Pulse)	-15	A
$I_B$	Base Current	-3.5	A
$P_C$	Collector Dissipation ( $T_a=25^\circ\text{C}$ )	2	W
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	30	W
$T_J$	Junction Temperature	150	°C
$T_{STG}$	Storage Temperature	-55 ~ 150	°C

\* PW≤300μs, Duty Cycle≤10%

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -60\text{V}, I_E = 0$		-10	μA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$		-10	μA
$h_{FE1}$	* DC Current Gain	$V_{CE} = -1\text{V}, I_C = -3\text{A}$	40	200	
$h_{FE2}$		$V_{CE} = -1\text{V}, I_C = -5\text{A}$	20		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}, I_B = -0.5\text{A}$		-0.5	V
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage	$I_C = -5\text{A}, I_B = -0.5\text{A}$		-1.5	V

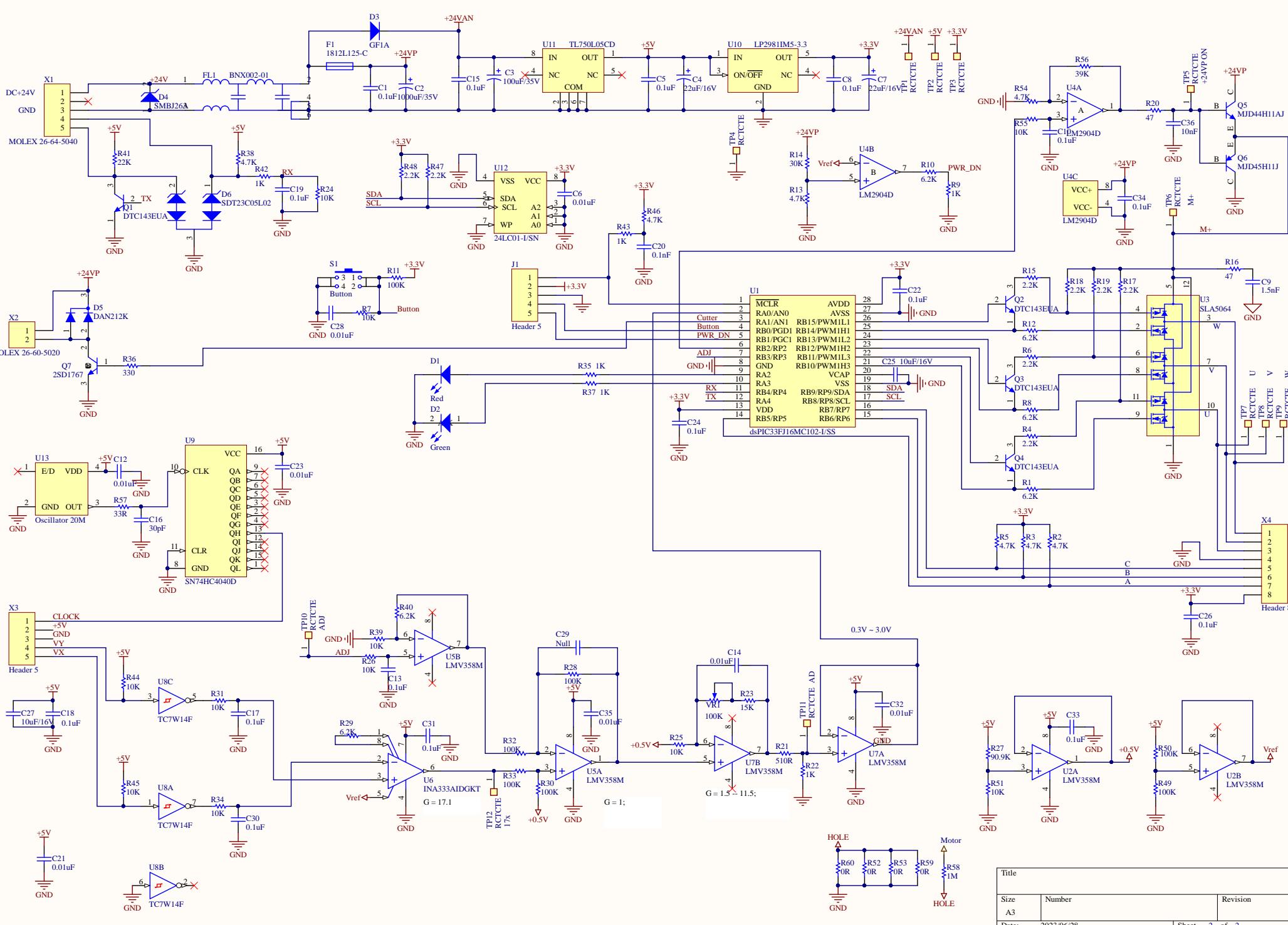
\* Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

代替型番DPak(TO-252-3)

MJD45H11AJ Nexperia  
MJD45H11J Nexperia  
MJD2955T4G onsemi  
MJD45H11T4G onsemi  
NJVMJD45H11G onsemi  
※TAB=コレクタ

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